



**Centre Interdisciplinaire de
Nanoscience de Marseille**



Luminy Campus-Marseille-France

FET ion sensor with Nanometric lipid gate insulator for high sensitivity detection level

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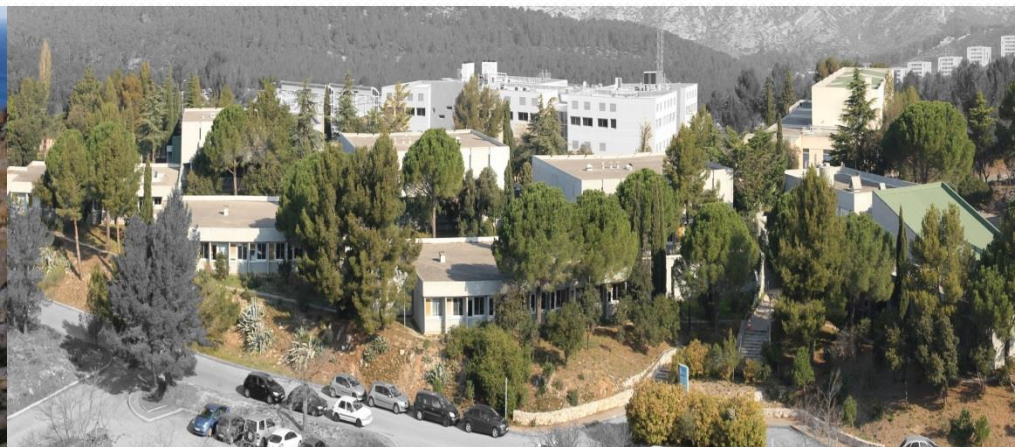


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Introduction

□ Heavy Metals

- Naturally occurring substances
- Present in environment at low levels
- Cant be degraded or destroyed
- Easily dissolved in water
 - Absorbed by aquatic organism
 - Contaminate drinking water and food
 - Affect human health



- 
- Detection of metals in human body
 - Early diagnosis of diseases (Case of Wilson disease: accumulation of copper in tissues)

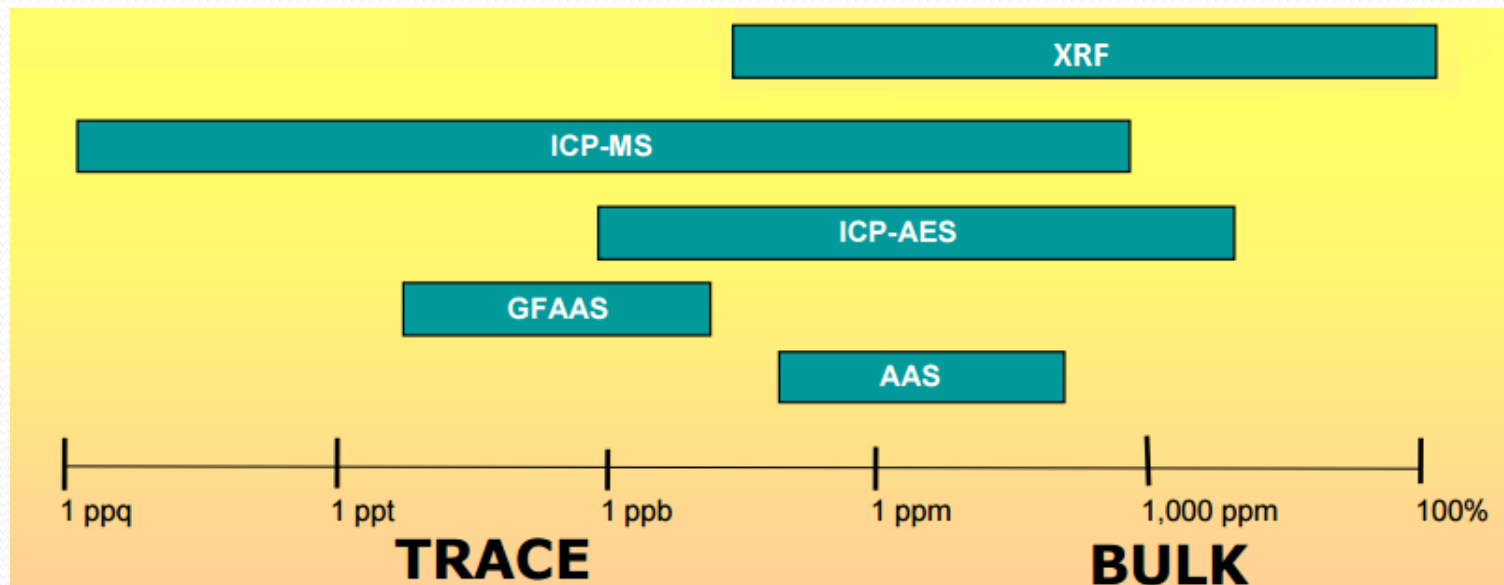


Introduction

□ Detection of metal ions

➤ Analytical methods:

- ICP-MS/AAS/XRF
- Expensive and large equipment
- Time consuming



1ppm=1mg/l

1ppb=1μg/l

1ppt=1ng/l

1ppq=1pg/l

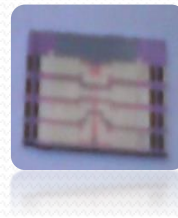
Introduction

□ New sensing Device

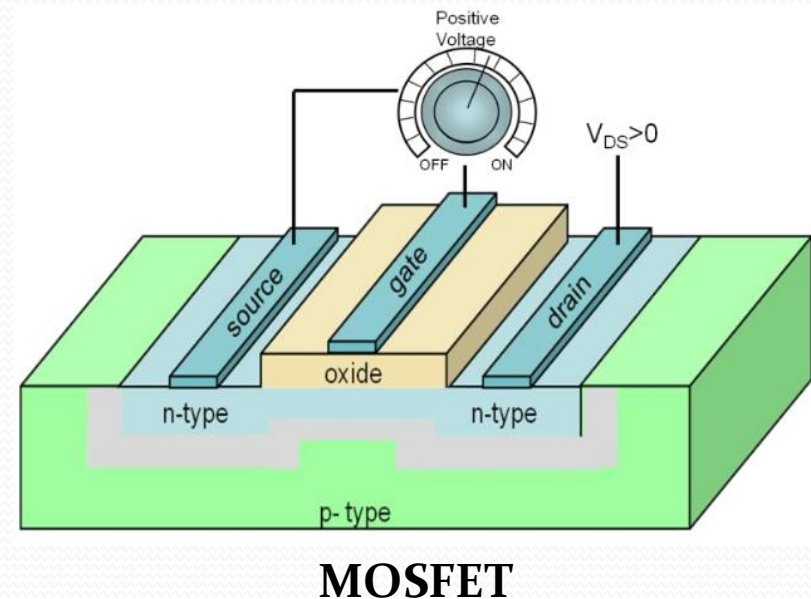
- Low cost
- Wearable , versatile
- Easy to use
- High detection level
- High specificity



□ Microdevice

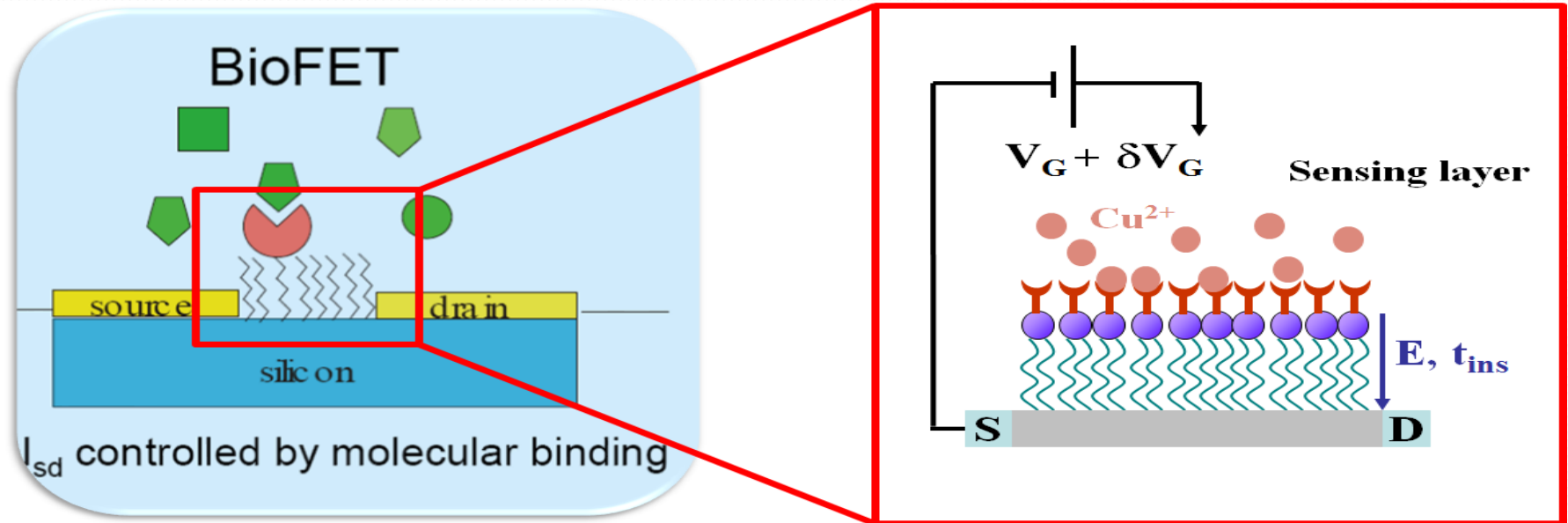


- Based on Field Effect Transistor (FET)
- Electrical detection



Field Effect Transistor Biosensor

From FET to bio-FET



Bio-FET Requirements

➤ Operating at low Voltage

- Preserve organic molecules

- Large Sensitivity $\frac{\delta V_G}{V_G}$

But!!!

E must be Large

$$E = \frac{V}{t_{ins}}$$

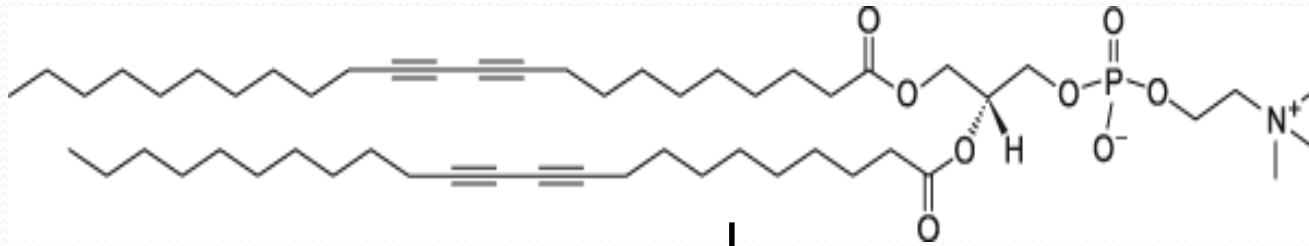
Diagram illustrating the relationship between electric field (E), voltage (V), and insulation thickness (t_{ins}). The equation is $E = \frac{V}{t_{ins}}$. Annotations indicate that E must be Large (green box), V must be Small (light blue box), and t_{ins} must be Small (red box).

□ Lipid Monolayer

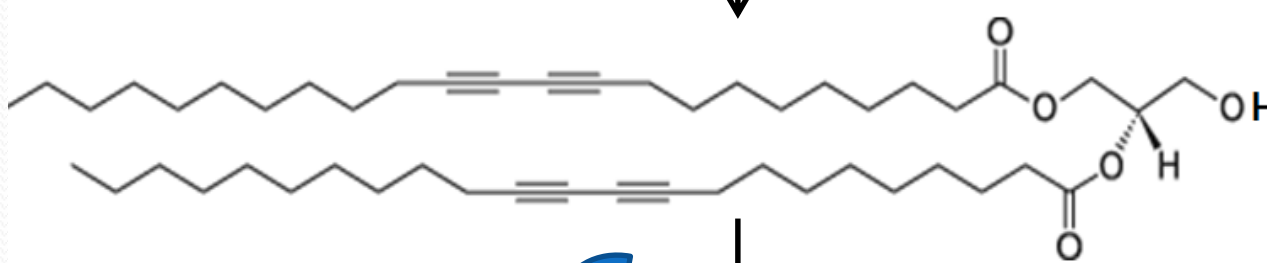
- Thickness: ~2.5 nm
- Natural ion barrier
- Dielectric properties (High electrical resistance $R \sim 1 \text{ G}\Omega$)
- Functionalization

Phospholipid

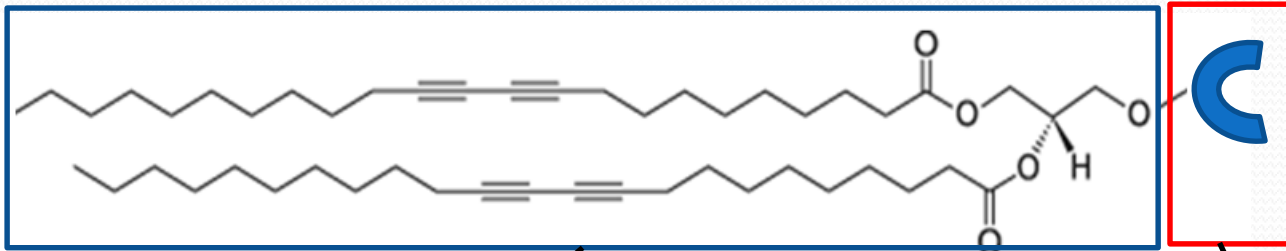
Functionalized lipid



Phospholipase C
H₂O, Over night, 50 °C

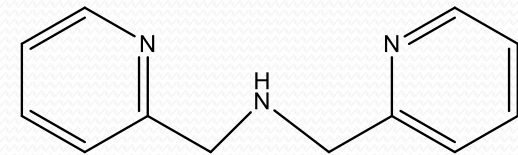


DCPC:2-Di-(10Z,12Z-tricosadiynoyl)-sn-Glycero-3-Phosphocholinephospholipid



Insulating part

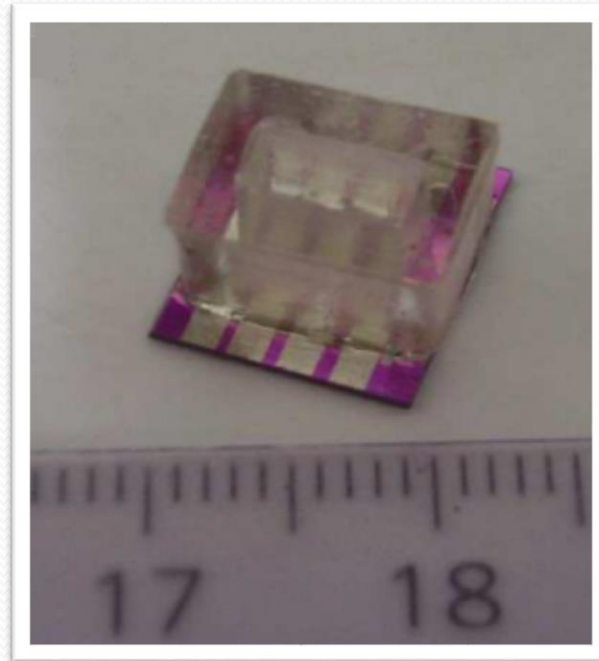
Sensing part



Dpa (dipicolylamine)

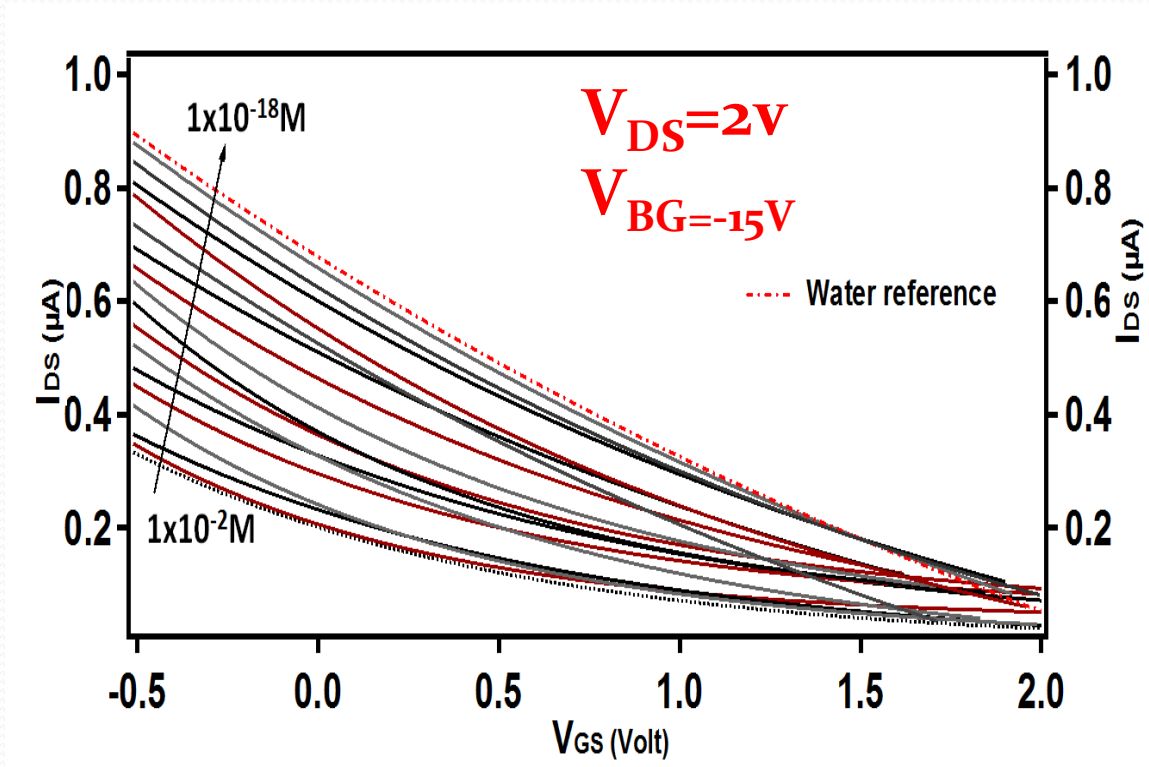
Our Devie

- 4 different separated Transistors with different channel length (600, 400, 200, 100 μm)
- PDMS ring



Sensitivity measurements

□ Sensitivity measurements



Variation of current (I_{DS}) vs V_{GS} with the increase in the concentration of copper (II)

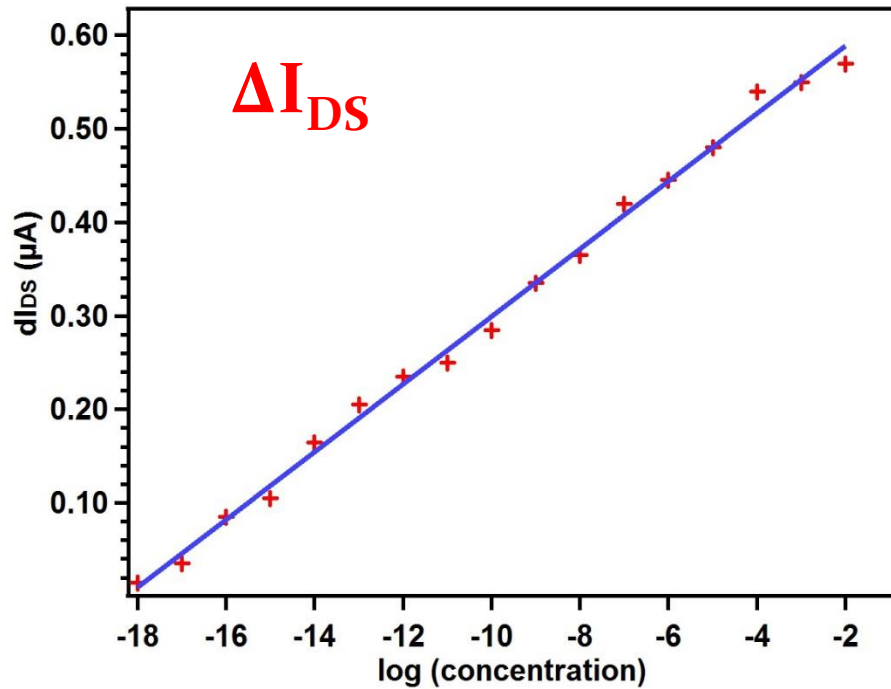
Detection range: $10^{-2} M$ (0.635g/l) to $10^{-18} M$ (1.57fg/l)



Super High sensitivity

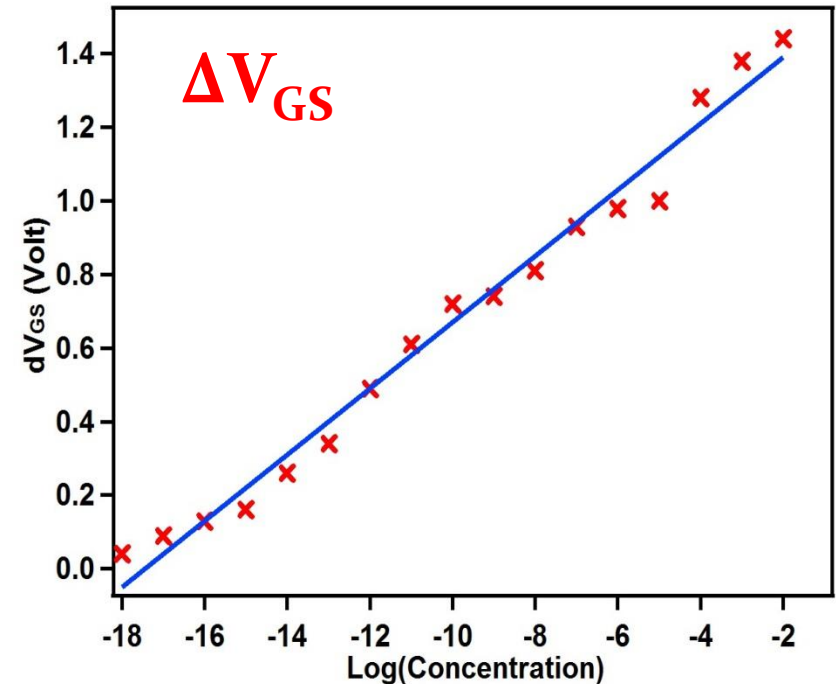
Sensitivity measurements

□ Sensitivity measurements



Variation of (ΔI_{DS}) with the increase in concentration of copper at $V_{GS} = -0.5V$

$$I_{DS} = 0.037 \mu A / \text{decade}$$



Variation of (ΔV_{GS}) with the increase in concentration of copper at $I_{DS} = 0.482 \mu A$

$$V_{GS} = 90 \text{ mV} / \text{decade}$$

Nernst Limit

□ Nernst equation

relates the potential of the sensitive ion electrode after capturing ions and the logarithm of the ion concentration in the bulk solution

$$\Delta V = -2.3 \frac{k_B T}{ze} \alpha \cdot \Delta pl$$

ΔV : detectable change in electrochemical potential

Δpl : = $-\log[\text{ion}]$

Z : Charge carried by the ion

k_B : Boltzmann constant

T : Temperature

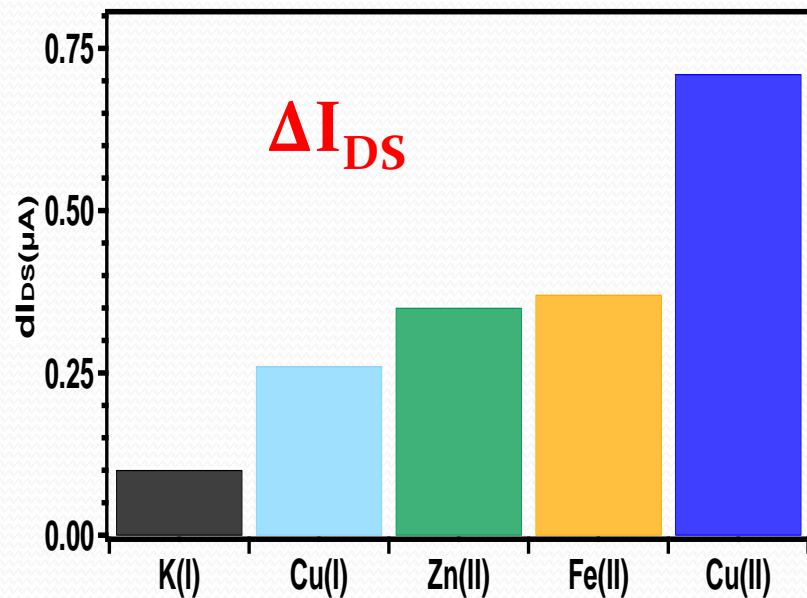
e : electrical charge

α : Sensitivity parameter

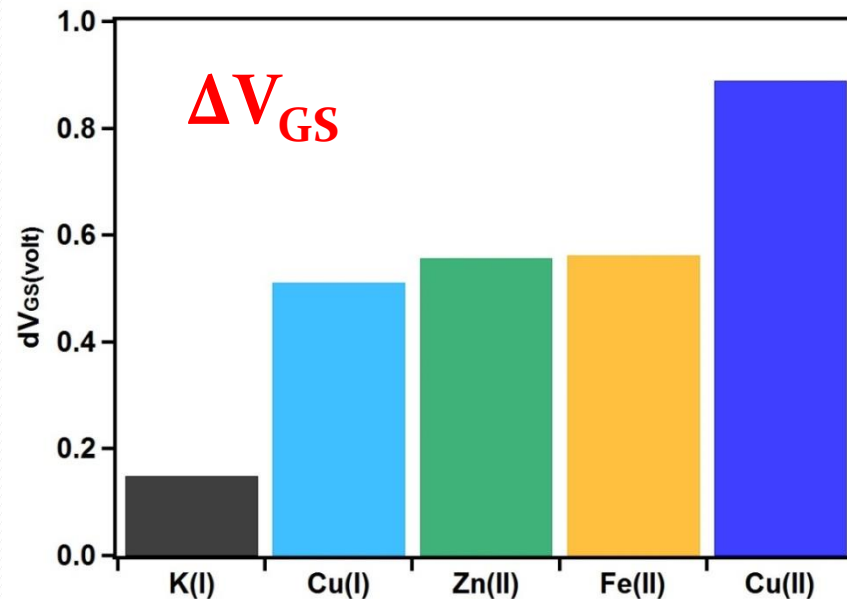
- Max detectable change in electrochemical potential according to Nernst equation for a divalent ion:
 $\Delta V = 29.5 \text{ mV/Decade}$
- Our device: $\Delta V = 90 \text{ mV/Decade}$

Super sensitivity exceeding Nernst limit

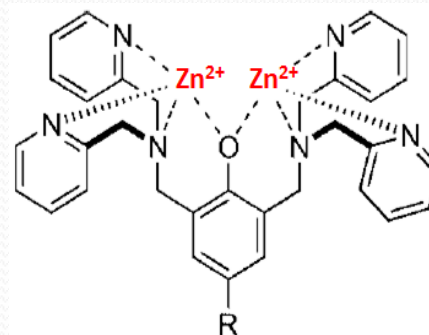
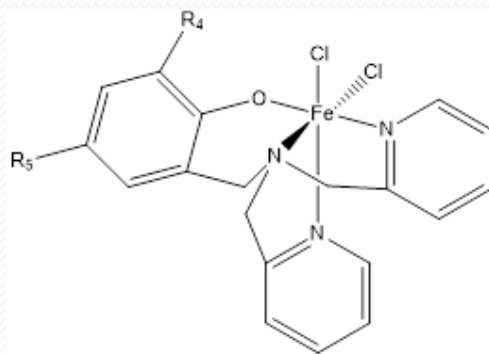
Selectivity measurements



Variation of (ΔI_{DS}) for different types of ions at $V_{GS} = -0.5V$

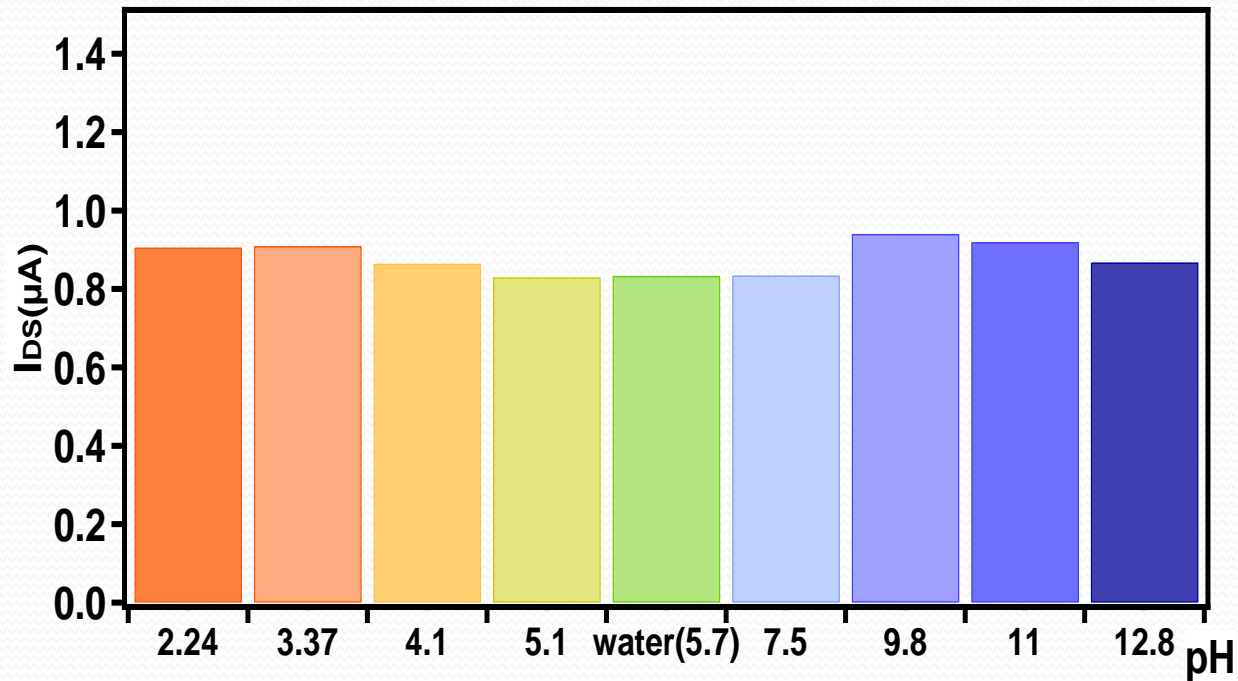


Variation of (ΔV_{GS}) for different types of ions at $I_{DS} = 0.6\mu A$



pH sensitivity

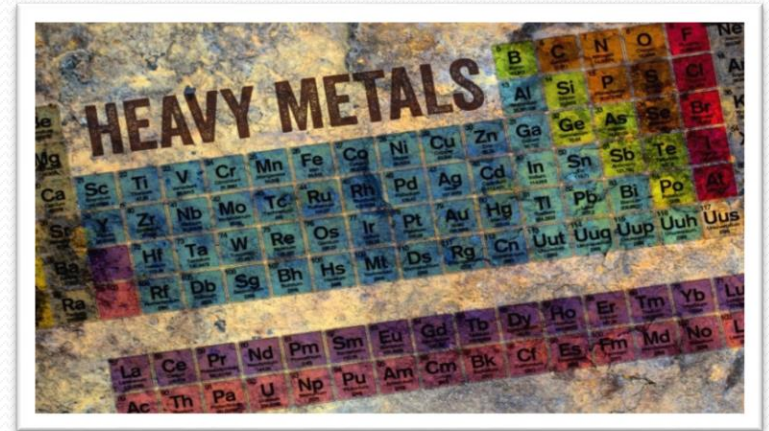
□ Effect of pH change



Variation of (I_{DS}) at different pH medium ranging from highly acidic to highly basic solution at $V_{GS} = -0.5V$

Conclusion and perspective

- Fabrication of BioFET device with super high sensitivity (detection range of Cu(II) from 10^{-2}M to 10^{-18}M) that exceeds Nernst limit
- Reasonable Selectivity toward Cu^{2+}
- Very stable under pH change
- Medical application: Test the device with biological sample (urine, blood, ...)
- Extend the measurements toward different ions



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